

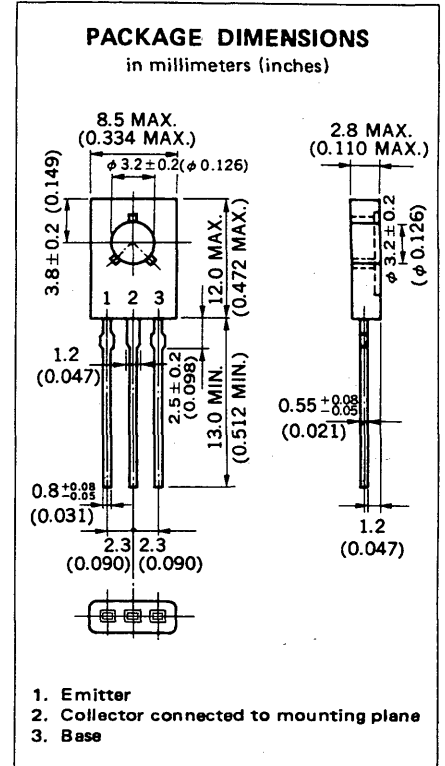
NPN SILICON POWER TRANSISTOR 2SC4001

DESCRIPTION The 2SC4001 is designed for uses of high-resolution monitor TV applications. This makes it possible to raise the video band of high-resolution monitor TVs to 50 MHz.

- FEATURES**
- High f_T : $f_T = 300$ MHz TYP. (@ $V_{CE} = 30$ V, $I_E = -30$ mA)
 - Low C_{ob} : $C_{ob} = 2.8$ pF (@ $V_{CB} = 30$ V)
 - High Voltage : $V_{CBO} = 300$ V, $V_{CEO} = 250$ V
 - High Total Power Dissipation :
 $P_T (T_a/T_c = 25^\circ\text{C}) = 1.3$ W/7 W
 - Complementary to 2SA1546

ABSOLUTE MAXIMUM RATINGS

Maximum Temperatures	
Storage Temperature	-55 to +150 °C
Junction Temperature	150 °C Maximum
Maximum Power Dissipation	
Total Power Dissipation ($T_a = 25^\circ\text{C}$)	1.3 W
Total Power Dissipation ($T_c = 25^\circ\text{C}$)	7.0 W
Maximum Voltages and Current ($T_a = 25^\circ\text{C}$)	
V_{CBO} Collector to Base Voltage	300 V
V_{CEO} Collector to Emitter Voltage	250 V
V_{EBO} Emitter to Base Voltage	5.0 V
I_C Collector Current	100 mA



ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

SYMBOL	CHARACTERISTIC	MIN.	TYP.	MAX.	UNIT	TEST CONDITIONS
h_{FE}	DC Current Gain	60	200	320		$V_{CE} = 10$ V, $I_C = 10$ mA*
f_T	Gain Bandwidth Product	200	300		MHz	$V_{CE} = 30$ V, $I_E = -30$ mA
C_{ob}	Output Capacitance		2.8	3.5	pF	$V_{CB} = 30$ V, $I_E = 0$, $f = 1$ MHz
I_{CBO}	Collector Cutoff Current			100	nA	$V_{CB} = 200$ V, $I_E = 0$
I_{EBO}	Emitter Cutoff Current			100	nA	$V_{EB} = 3.0$ V, $I_C = 0$
$V_{CE(sat)}$	Collector Saturation Voltage		0.08	0.3	V	$I_C = 10$ mA, $I_B = 1.0$ mA*
$V_{BE(sat)}$	Base Saturation Voltage		0.72	1.2	V	$I_C = 10$ mA, $I_B = 1.0$ mA*
V_{ESDR}	Electrostatic Discharge-Resistant		1 000		V	$C = 1$ 000 pF, E-B Reverse Bias

* Pulsed PW ≤ 350 μ s, Duty Cycle ≤ 2 %

Classification of h_{FE}

Rank	M	L	K
Range	60 to 120	100 to 200	160 to 300

Test Conditions: $V_{CE} = 10$ V, $I_C = 10$ mA

TYPICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

